

a conductive layer formed on said semiconductor substrate and including polycrystals, said conductive layer including in its surface a recess caused by a crystal grain boundary and having side walls formed such that a distance therebetween becomes small as closer to said semiconductor substrate, wherein said conductive layer includes:

a first conductive layer having a substantially planar upper surface, formed on said semiconductor substrate and including a polycrystal having a first average grain size;

a second conductive layer formed on said first conductive layer, including a polycrystal having a second average grain size greater than said first average grain size and having said recess; and

said recess is formed directly over the substantially planar upper surface of the first conductive layer.

Please cancel claim 2.

REMARKS

Claims 1 and 3 through 10 are pending in this application. Claim 1 has been amended by incorporating the limitations of claim 2 therein and further specifying that the recess is formed directly over the substantially planar upper surface of the first conductive layer, adequate descriptive support for which should be apparent throughout the originally filed disclosed as, for example, Fig. 1A and the related discussion thereof in the written description of the specification. Applicants submit that the present Amendment does not generate any new matter issue.

A clean copy of the title and amended claim 1 appears in the Appendix hereto.